

Title (en)

SEMICONDUCTORS CONTAINING PERFLUOROETHER ACYL OLIGOTHIOPHENE COMPOUNDS

Title (de)

HALBLEITER, ENTHALTEND PERFLUORETHERACYLOLIGOTHIOPHEN-VERBINDUNGEN

Title (fr)

SEMI-CONDUCTEURS CONTENANT DES COMPOSES OLIGOTHIOPHENE ACYLES A SUBSTITUTION PERFLUOROETHER

Publication

EP 1877462 A1 20080116 (EN)

Application

EP 06735988 A 20060223

Priority

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- US 7597805 A 20050309
- US 7626805 A 20050309

Abstract (en)

[origin: WO2006098859A1] Semiconductor devices are described that include a semiconductor layer that comprises a perfluoroether acyl oligothiophene compound, preferably an a,?-bis-perfluoroether acyl oligothiophene compound. Additionally, methods of making semiconductor devices are described that include depositing a semiconductor layer that contains a perfluoroether acyl oligothiophene compound, preferably an a,?-bis(2- perfluoroether acyl oligothiophene compound.

IPC 8 full level

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CPC (source: EP KR)

B82Y 30/00 (2013.01 - EP); **C07D 333/22** (2013.01 - EP KR); **C07D 333/28** (2013.01 - EP KR); **C08G 61/12** (2013.01 - KR); **H10K 85/113** (2023.02 - EP); **H10K 85/655** (2023.02 - EP); **H10K 99/00** (2023.02 - KR); **H10K 10/466** (2023.02 - EP); **H10K 10/474** (2023.02 - EP)

Citation (search report)

See references of WO 2006098859A1

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